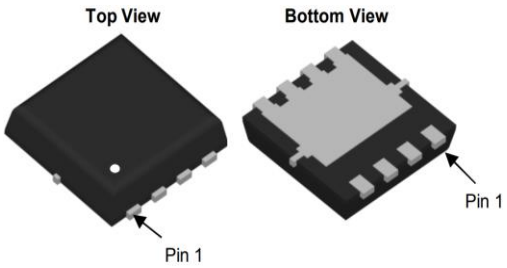
30V/30A N-Channel MOSFET

Product Summary

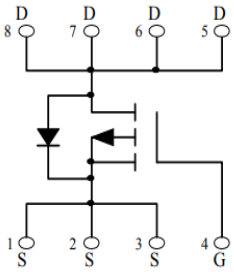
BVDSS	30	V
ID	30	A
RDSON@VGS=10V	9.5	mΩ
RDSON@VGS=4.5V	16.0	mΩ

PDFN3X3-8L



Features

- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS



Schematic diagram

Application

- Battery and loading switching
- Excellent package for good heat dissipation

Ordering Information:

Product	Package	Marking	Packing
M03N30Q	PDFN3x3-8L	PTN7530	5000PCS/Reel

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	30	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ 10V[1]	10	A
I_{DM}	Pulsed Drain Current[2]	90	A
EAS	Single Pulse Avalanche Energy[3]	19	mJ
I_{AS}	Avalanche Current	25	A
P_D@T_A=25°C	Total Power Dissipation[4]	10	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	85	°C/W

30V/30A N-Channel MOSFET

Electrical Characteristics(Ta=25℃)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=10A	-	9.5	13	mΩ
		V_{GS}=4.5V, I_D=5A	-	16	22.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1.0MHz	-	633	-	pF
C_{oss}	Output Capacitance		-	120	-	pF
C_{rss}	Reverse Transfer Capacitance		-	99	-	pF
Q_g	Total Gate Charge	V_{DS}=15V, I_D=10A, V_{GS}=10V	-	15	-	nC
Q_{gs}	Gate-Source Charge		-	4.7	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	3.6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=30V,I_D=18A, R_{GEN}=3Ω, V_{GS}=10V	-	5	-	ns
t_r	Turn-on Rise Time		-	8	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	21	-	ns
t_f	Turn-off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	18	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	72	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=18A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=18A,dI/dt=100A/μs	-	7	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	5.9	-	nC

Note :

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZcopper.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦2%
3. The EAS data shows Max. rating . The test condition isV_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=20A
4. The power dissipation is limited by 150℃ junctiontemperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

30V/30A N-Channel MOSFET

Typical Characteristics

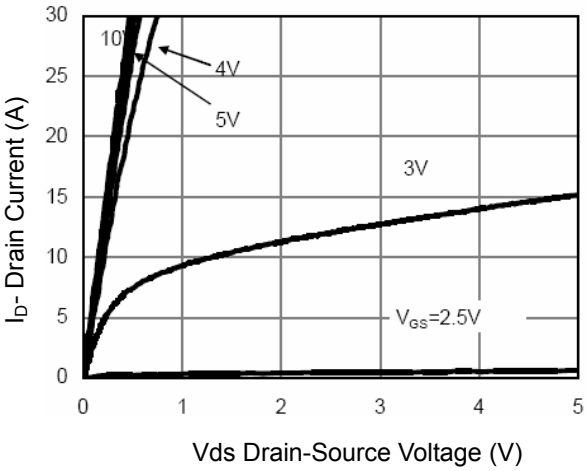


Figure 1 Output Characteristics

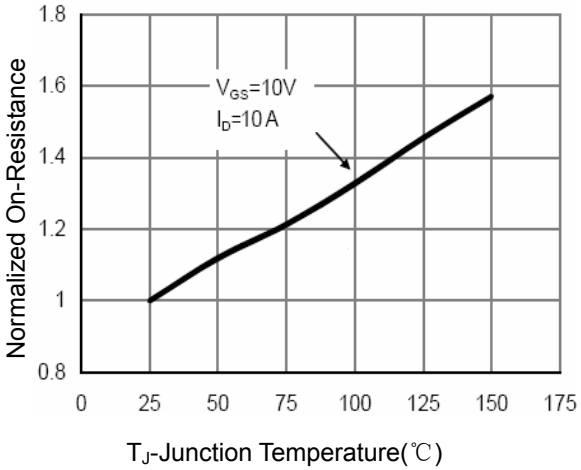


Figure 4 Rdson-Junction Temperature

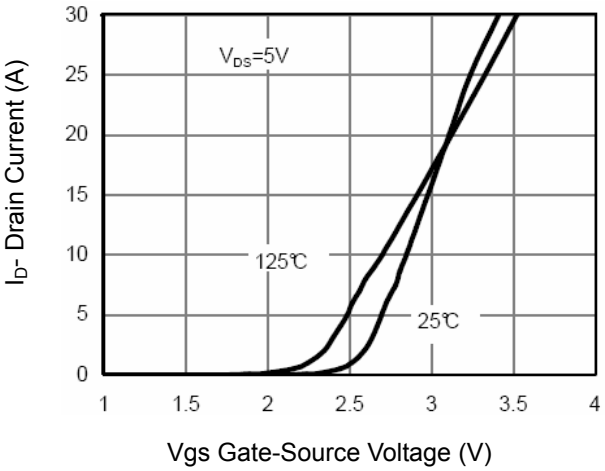


Figure 2 Transfer Characteristics

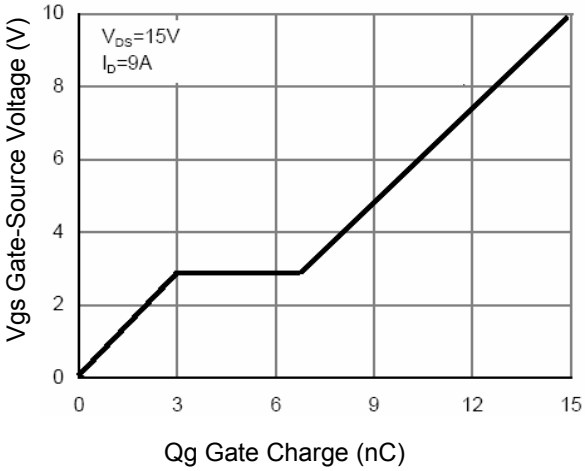


Figure 5 Gate Charge

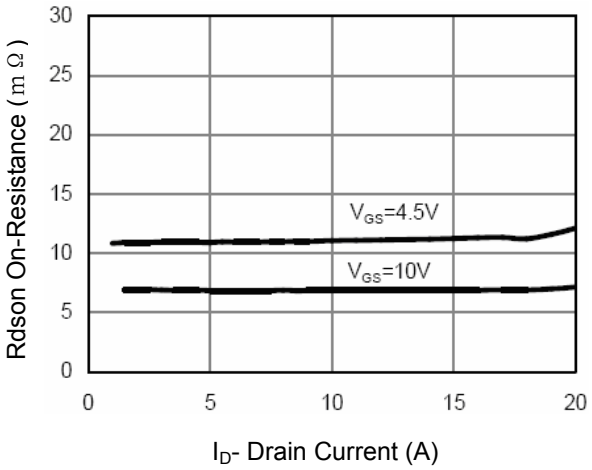


Figure 3 Rdson- Drain Current

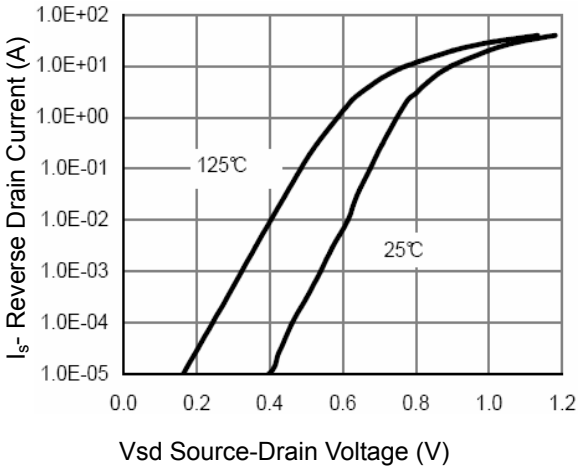


Figure 6 Source- Drain Diode Forward

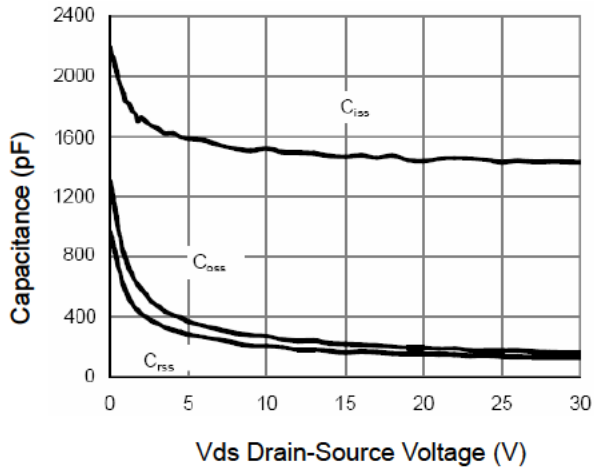


Figure 7 Capacitance vs Vds

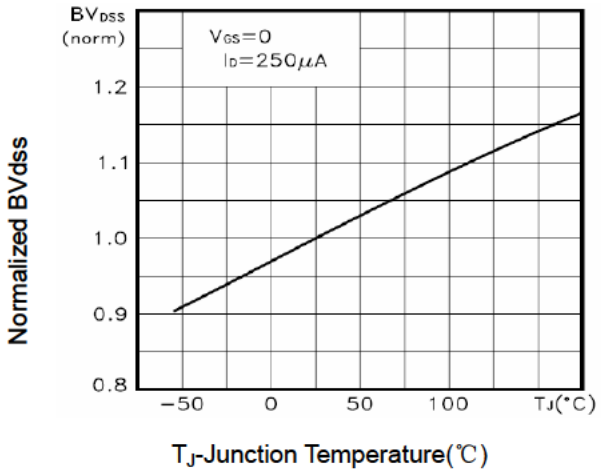


Figure 9 BV_{DSS} vs Junction Temperature

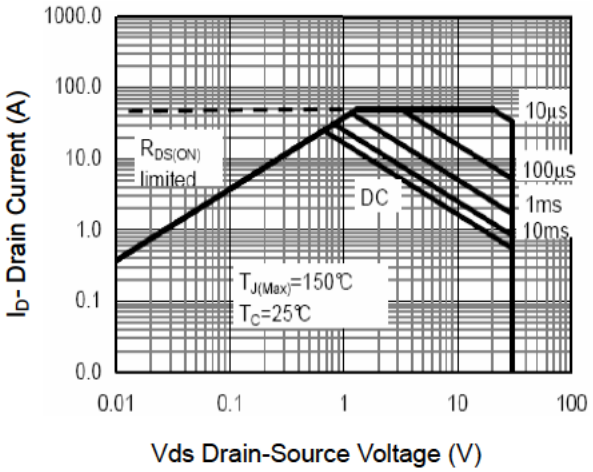


Figure 8 Safe Operation Area

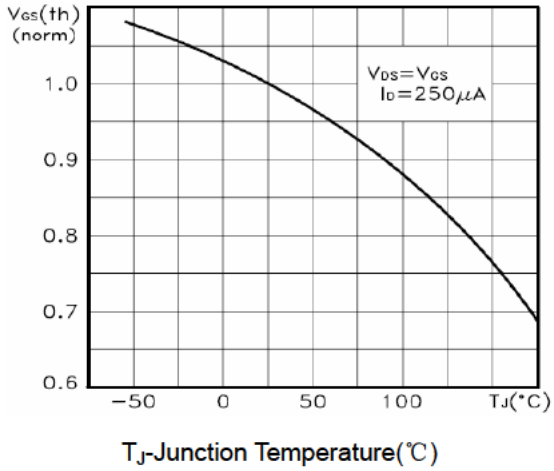


Figure 10 $V_{GS(th)}$ vs Junction Temperature

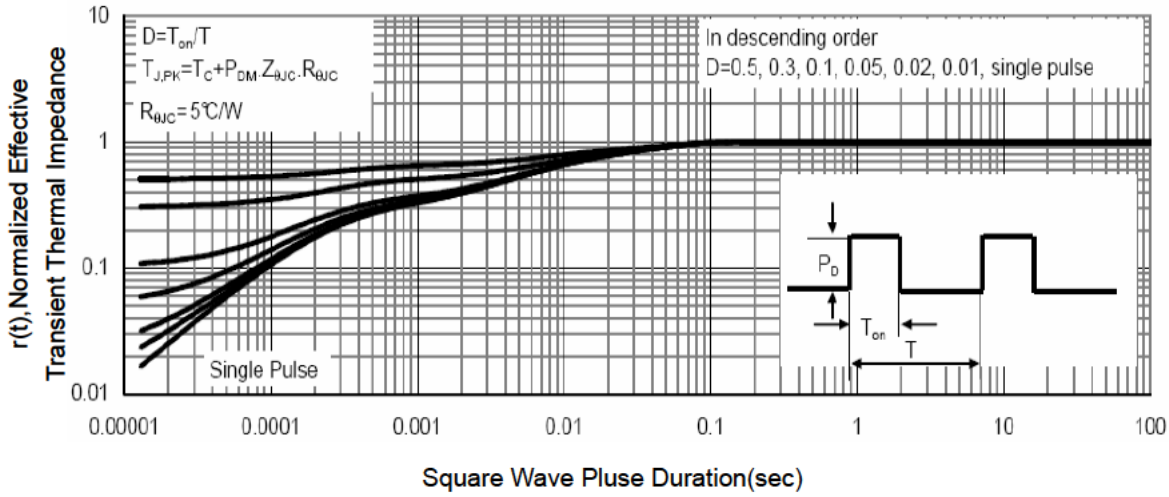
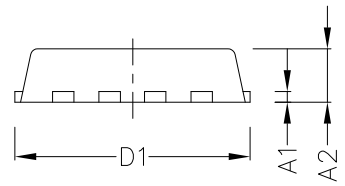


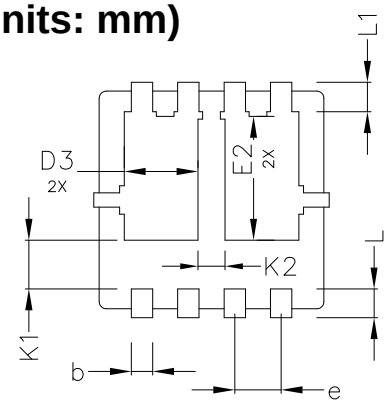
Figure 11 Normalized Maximum Transient Thermal Impedance

30V/30A N-Channel MOSFET

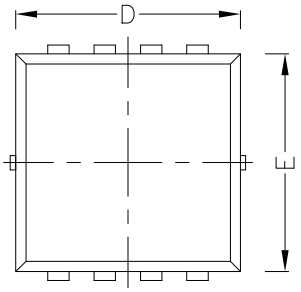
PDFN3333Package Outline Dimensions (Units: mm)



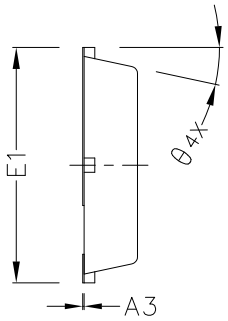
SIDE VIEW



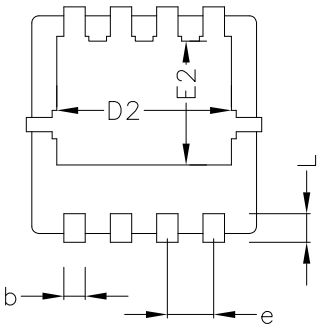
BOTTOM VIEW
OPTION 2



TOP VIEW



SIDE VIEW



BOTTOM VIEW
OPTION 1

COMMON DIMENSIONS
(UNITS OF MEASURE IS mm)

	MIN	NORMAL	MAX
A1		0.152 BSC	
A2	0.650	0.750	0.850
A3	0.005	–	0.020
b	0.250	0.300	0.350
D	2.950	3.050	3.150
D1	3.000	3.150	3.250
D2	2.350	2.450	2.550
D3	0.935	1.035	1.135
E1	3.150	3.300	3.450
E	2.950	3.050	3.150
E2	1.635	1.735	1.935
e		0.650 TYPE	
L	0.300	0.400	0.500
θ		12° TYPE	
K1		0.680 REF	
K2		0.380 REF	
L1		0.410 REF	